NSN 5961-00-324-3211

Demilitarization:

No Fiig: A110a0

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-324-3211 **Inclosure Material:** Metal **Overall Length:** 1.000 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-83 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 1.031 inches and 1.062 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 60.0 repetitive peak reverse voltage and 75.0 nonrepetitive peak reverse voltage and 50.0 breakover voltage, dc **Current Rating Per Characteristic:** 6.50 milliamperes forward current, average minor and 6.50 milliamperes forward current, average watts and 100.00 milliamperes forward current, total rms peak and 110.00 amperes forward current, total rms horsepower metric and 70.00 amperes forward current, total rms universal and 1000.00 amperes forward current, total rms watts **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure:**